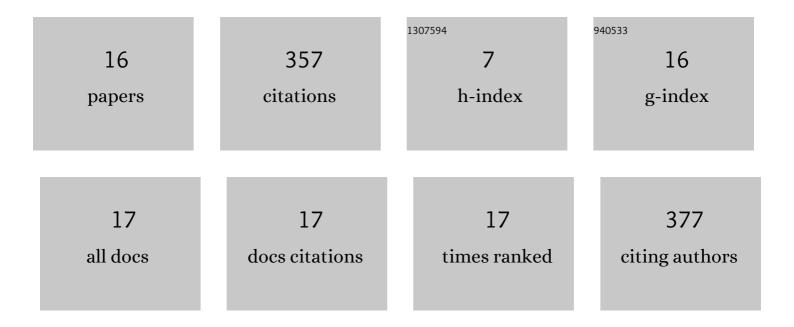


List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Self-Assembly Nanopillar/Superlattice Hierarchical Structure: Boosting AlGaN Crystalline Quality and Achieving High-Performance Ultraviolet Avalanche Photodetector. ACS Applied Materials & Interfaces, 2022, 14, 33525-33537.	8.0	4
2	High-performance normally off p-GaN gate high-electron-mobility transistor with In0.17Al0.83N barrier layer design. Optical and Quantum Electronics, 2021, 53, 1.	3.3	7
3	Progress on AlGaN-based solar-blind ultraviolet photodetectors and focal plane arrays. Light: Science and Applications, 2021, 10, 94.	16.6	193
4	A High Quantum Efficiency Narrow-Band UV-B AlGaN p-i-n Photodiode With Polarization Assistance. IEEE Photonics Journal, 2021, 13, 1-8.	2.0	5
5	Low-Voltage p-i-n GaN-Based Alpha-Particle Detector With High Energy Resolution. IEEE Electron Device Letters, 2021, 42, 1755-1758.	3.9	3
6	Direct observation of reach-through behavior in back-illuminated algan avalanche photodiode with separate absorption and multiplication structure. Journal Physics D: Applied Physics, 2020, 53, 425101.	2.8	3
7	Îμ-Ga2O3: A Promising Candidate for High-Electron-Mobility Transistors. IEEE Electron Device Letters, 2020, , 1-1.	3.9	15
8	Back-illuminated AlGaN heterostructure solar-blind avalanche photodiodes with one-dimensional photonic crystal filter. Optics Express, 2020, 28, 6027.	3.4	7
9	A High-Performance SiO ₂ /SiN <i> _x </i> 1-D Photonic Crystal UV Filter Used for Solar-Blind Photodetectors. IEEE Photonics Journal, 2019, 11, 1-7.	2.0	3
10	Nanoplasmonically Enhanced High-Performance Metastable Phase α-Ga ₂ O ₃ Solar-Blind Photodetectors. ACS Applied Materials & Interfaces, 2019, 11, 40283-40289.	8.0	31
11	Performance Modulation for Back-Illuminated AlGaN Ultraviolet Avalanche Photodiodes Based on Multiplication Scaling. IEEE Photonics Journal, 2019, 11, 1-7.	2.0	10
12	Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. ACS Applied Materials & Interfaces, 2019, 11, 20956-20964.	8.0	39
13	Effects of the Trap Level in the Unintentionally Doped GaN Buffer Layer on Optimized pâ€GaN Gate AlGaN/GaN HEMTs. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700368.	1.8	5
14	An Improved Design for Solar-Blind AlGaN Avalanche Photodiodes. IEEE Photonics Journal, 2017, 9, 1-7.	2.0	13
15	Photoluminescence Study of the Photoinduced Phase Separation in Mixed-Halide Hybrid Perovskite CH3NH3Pb(Brxl1â~x)3 Crystals Synthesized via a Solvothermal Method. Scientific Reports, 2017, 7, 17695.	3.3	18
16	Improved Schottky contacts to InGaN alloys by a photoelectrochemical treatment. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1034-1038.	1.8	0